

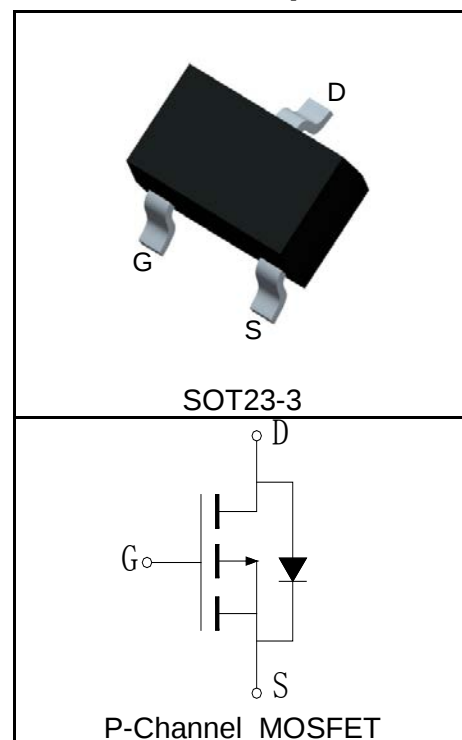
Features

- -25V/-4A,
 $R_{DS(ON)} = 45m\Omega(Typ.)@V_{GS}=-10V$
 $R_{DS(ON)} = 55m\Omega(Typ.)@V_{GS}=-4.5V$
 $R_{DS(ON)} = 75m\Omega(Typ.)@V_{GS}=-2.5V$
- Low On-Resistance
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Load Switch
- DC/DC Converter

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	-25	V
V_{GSS}	Gate-Source Voltage	± 16	
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
I_S	Diode Continuous Forward Current	$T_A = 25^\circ C$	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_A = 25^\circ C$	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=-10V$)	$T_A = 25^\circ C$	A
		$T_A = 70^\circ C$	
P_D	Maximum Power Dissipation	$T_A = 25^\circ C$	W
		$T_A = 70^\circ C$	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	-	$^\circ C/W$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	100	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	-	mJ

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU30P4C			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-25	-30		V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-25V, V _{GS} =0V			-1	μA
			T _J =125°C			
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.9	-1.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-4A		45	52	mΩ
		V _{GS} =-4.5V, I _{DS} =-3.2A		55	65	mΩ
		V _{GS} =-2.5V, I _{DS} =-2.4A		75	90	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V			-1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =-4A, dI _{SD} /dt=100A/μs		12		ns
Q _{rr}	Reverse Recovery Charge			4		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		1.2		Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		585		pF
C _{oSS}	Output Capacitance			90		
C _{rSS}	Reverse Transfer Capacitance			50		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _L =3.8Ω, I _{DS} =-4A, V _{GEN} =-10V, R _G =6Ω		7		ns
t _r	Turn-on Rise Time			4		
t _{d(OFF)}	Turn-off Delay Time			40		
t _f	Turn-off Fall Time			8		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =-24V, V _{GS} =-10V, I _{DS} =-4A		12		nC
Q _{gs}	Gate-Source Charge			1.5		
Q _{gd}	Gate-Drain Charge			2.4		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} . Starting $T_J = 25^{\circ}\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Marking ^①	Package	Packaging	Quantity	Reel Size	Tape width
RU30P4C	BXYWW	SOT23-3	Tape&Reel	3000	7"	8mm

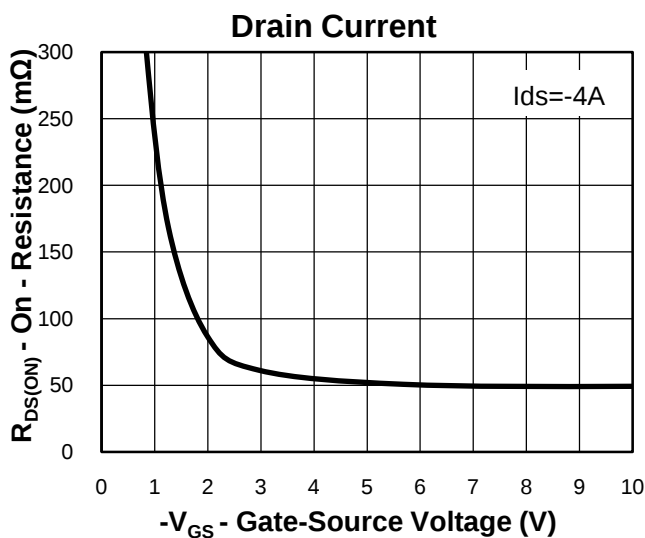
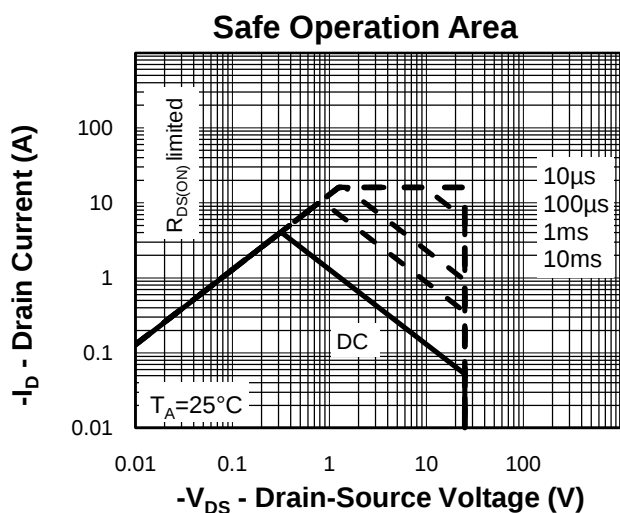
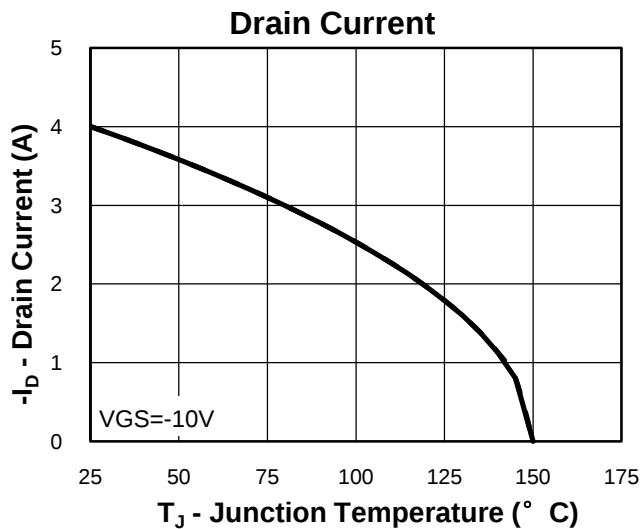
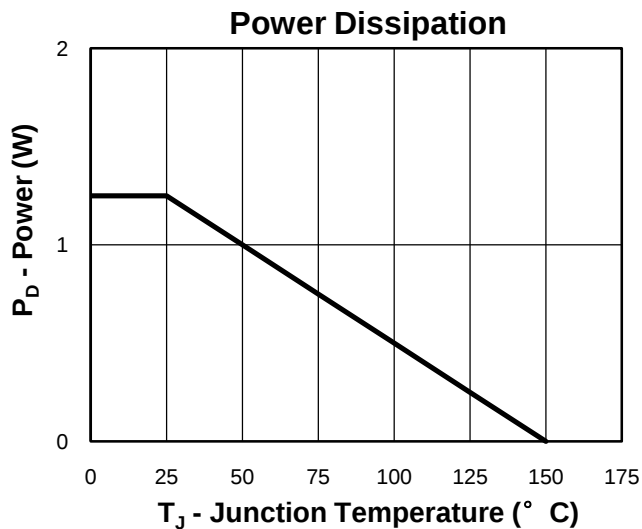
① The following characters could be different and means:

X =Assembly site code

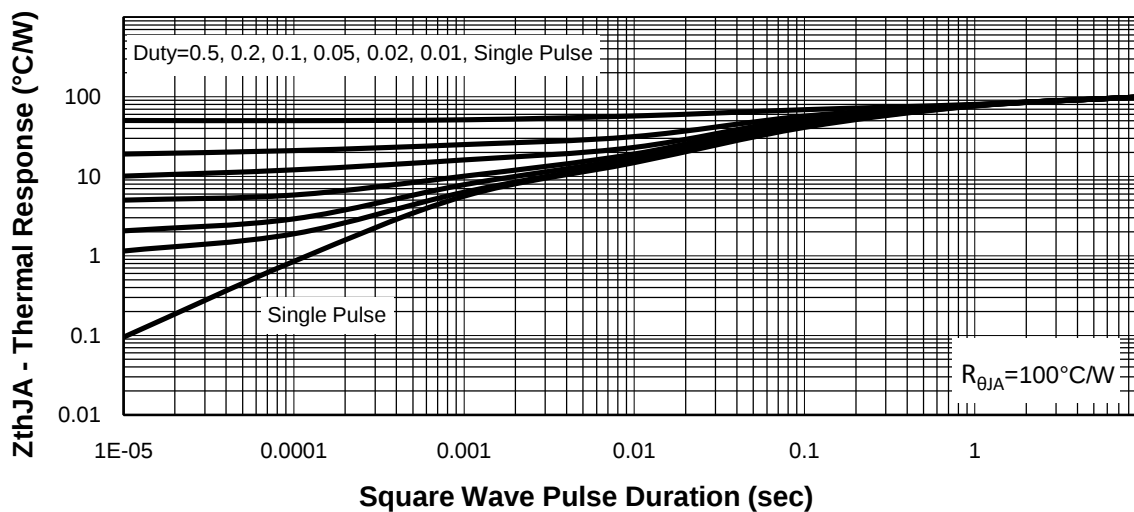
Y =Year

WW =Work Week

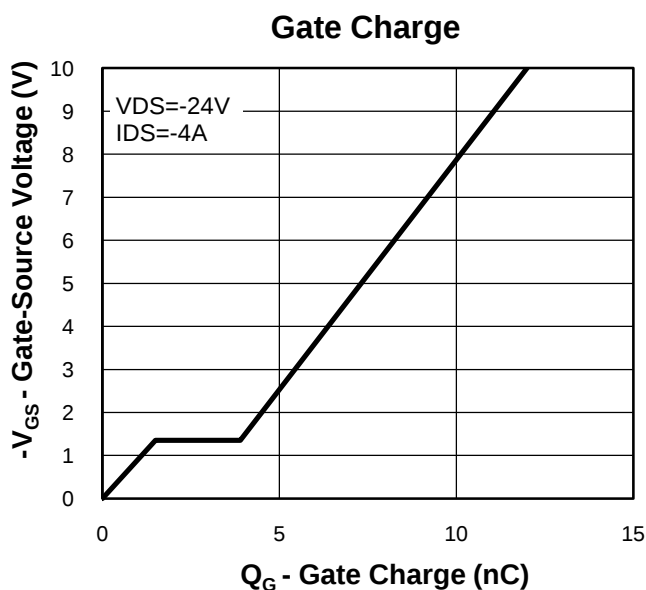
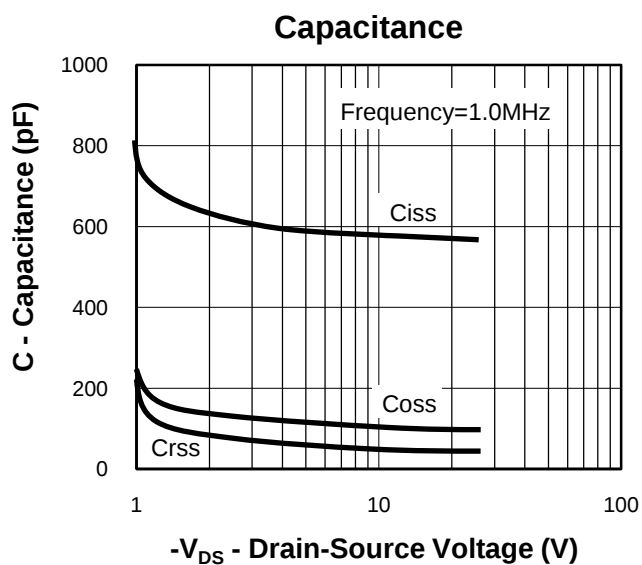
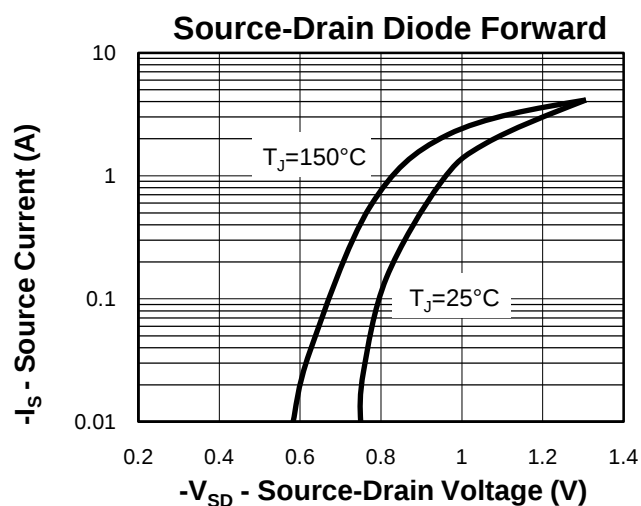
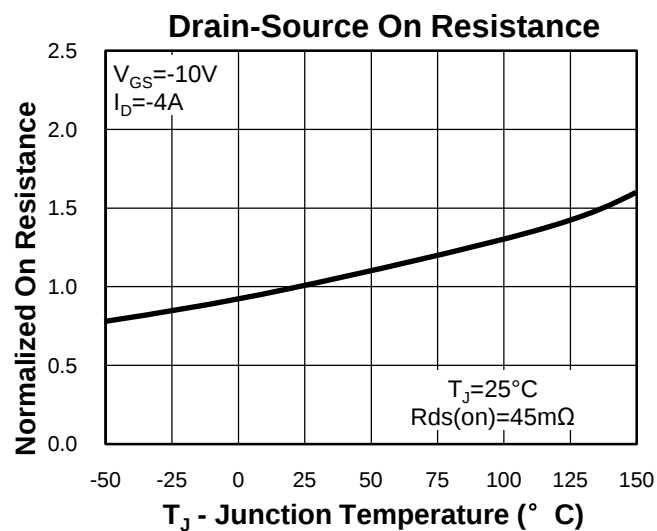
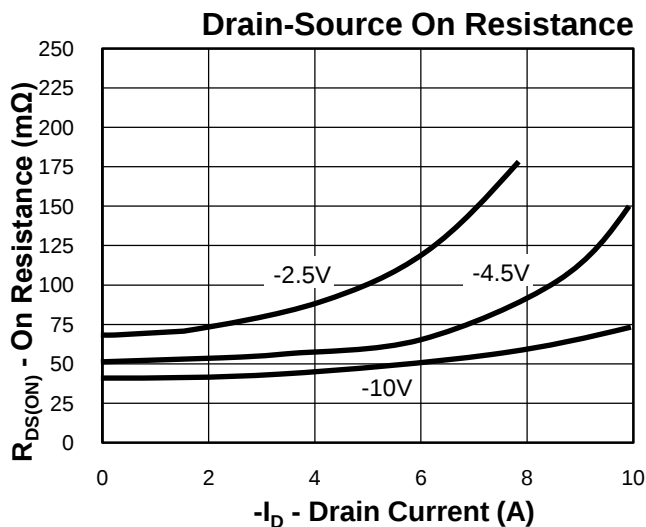
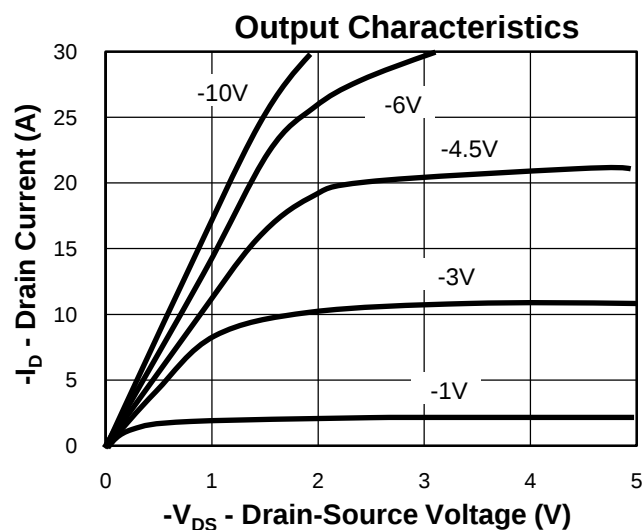
Typical Characteristics



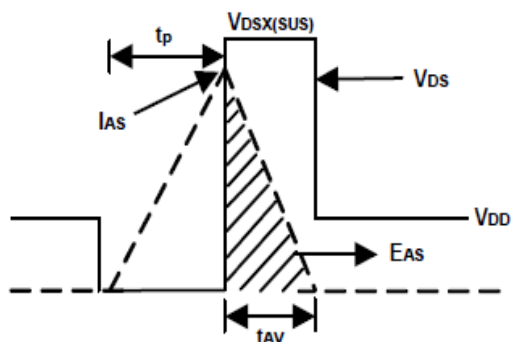
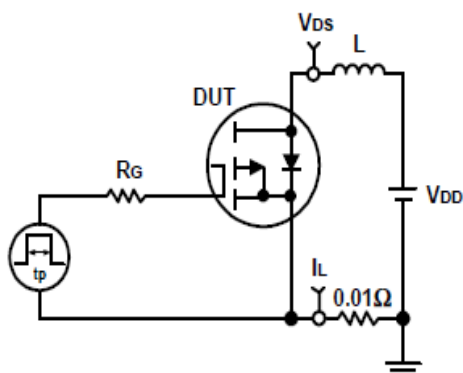
Thermal Transient Impedance



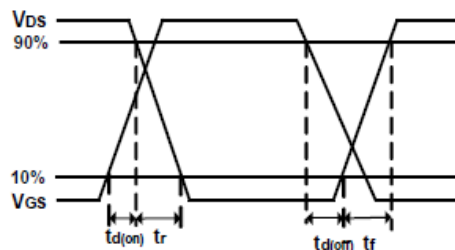
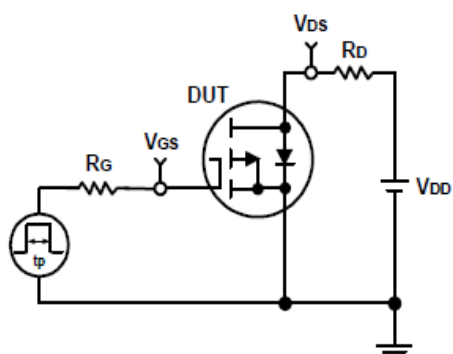
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Avalanche Test Circuit and Waveforms

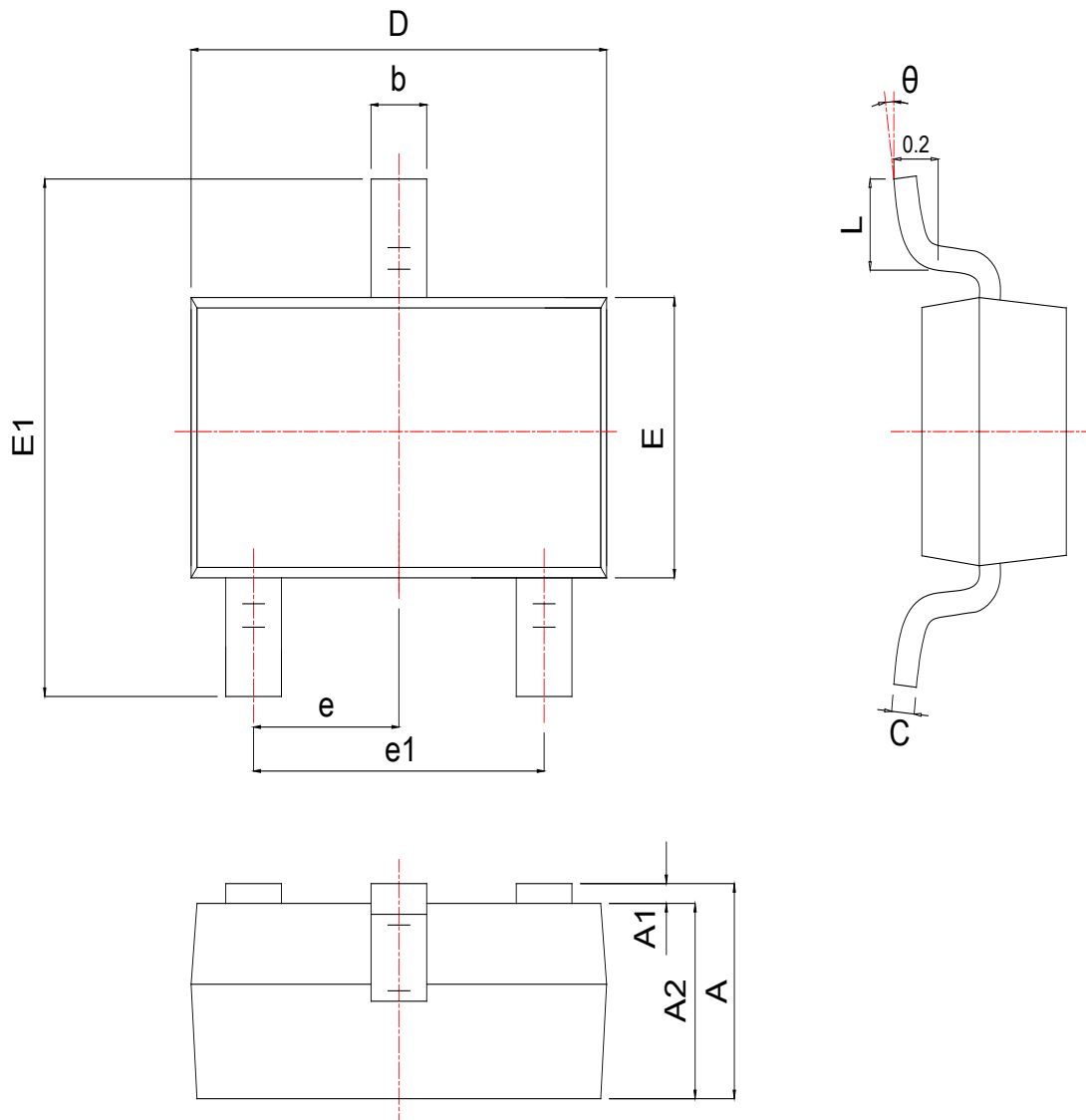


Switching Time Test Circuit and Waveforms



Package Information

SOT23-3



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.050	1.150	1.250	0.041	0.045	0.049
A1	0.000	0.050	0.100	0.000	0.002	0.004
A2	1.050	1.100	1.150	0.041	0.043	0.045
b	0.300	0.400	0.500	0.012	0.016	0.020
c	0.100	0.150	0.200	0.004	0.006	0.008
D	2.820	2.920	3.020	0.111	0.115	0.119
E	1.500	1.600	1.700	0.059	0.063	0.067
E1	2.650	2.800	2.950	0.104	0.110	0.116
e	0.950 BSC			0.037 BSC		
e1	1.800	1.900	2.000	0.071	0.075	0.079
L	0.300	0.450	0.600	0.012	0.018	0.024
θ	0°	4°	8°	0°	4°	8°

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